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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet	1	of	1	Attorney Docket Number	543822002600
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**Complete if Known**

Application Number	10/722,576
Filing Date	November 28, 2003
First Named Inventor	Thomas Happ
Art Unit	2187
Examiner Name	K. N. McLean Mayo

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
	1.	2003/0084233-A1	05-01-2003	WILLIAMS	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				

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**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	2.	Hirose, Y. et al. (1976). "Polarity-dependent Memory Switching and Behavior of Ag Dendrite in Ag-photodoped Amorphous As <sub>2</sub> S <sub>3</sub> Films," <i>Journal of Applied Physics</i> 47(6):2767-2772.	
	3.	Kozicki, M. N. et al. (1999). "Application of Programmable Resistance Changes in Metal-doped Chalcogenides," <i>Electrochemical Society Proceedings</i> 99(13):298-309.	
	4.	Kozicki, M. N. et al. (2000). "Nanoscale Effects in Devices Based on Chalcogenide Solid Solutions," <i>Superlattices and Microstructures</i> 27(5/6):485-488.	
	5.	Kozicki, M. N. et al. (2002). "Can Solid State Electrochemistry Eliminate the Memory Scaling Quandry," <i>Proc. VLSI</i> 15 pages.	
	6.	Neale, R. (2002). "Micron to Look Again at Non-volatile Amorphous Memory," <i>Electronic Engineering Design</i> 6 pages.	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Signature		Date Considered	
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